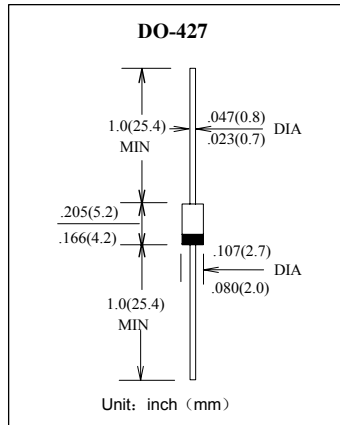




DB3

双向触发二极管

SILICON BIDIRECTIONAL DIAC



Features

- Low reverse leakage
- High forward surge capability
- High temperature soldering guaranteed:
21 €
250°C/10 seconds, 0.375" (9.5mm) lead length,
- 5 lbs. (2.3kg) tension

Mechanical Data

- Terminals: Plated axial leads
- Polarity: Color band denotes cathode end
- Mounting Position: Any

ABSOLUTE RATINGS (LIMITING VALUES)

Symbols	Parameters		Value	Units
			DB3	
P_c	Power Dissipation on Printed Circuit [L=10mm]	$T_A=50^\circ\text{C}$	150	mW
I_{TRM}	Repetitive Peak on-state Current	$t_p=10s$ $F=100\text{Hz}$	2.0	A
T_{STG}/T_J	Storage and 0 perating Junction Temperature		-40 to +125 / -40 to 110	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS

Symbols	Parameters	Test Conditions	Value	Units	
			DB3		
V_{BO}	Breakover Voltage [Note 2]	$C=22\text{nF}$ [Note 2] See Diagram 1	Min Typ Max	28 32 36	V
$I + V_{BO}$ $I - V_{BO}$	Breakover Voltage Symmetry	$C=22\text{nF}$ [Note 2] See Diagram 1	Max	± 3	V
$I \pm \Delta V$	Dynamic Breakover Voltage [Note 1]	$\Delta I=[I_{BO} \text{ to } I_F=10\text{mA}]$ See Diagram 1	Min	5	V
V_o	Output Voltage [Note 1]	See Diagram 2	Min	5	V
I_{BO}	Breakover Current [Note 1]	$C=22\text{nF}$ [Note 2]	Max	100	μA
t_r	Rise Time [Note 1]	See Diagram 3	Typ	1.5	S
I_B	Leakage Current [Note 1]	$V_{BBO}=0.5\text{V max}$ See Diagram 1	Max	10	μA

Notes:1.Electrical characteristics applicable in both forward and reverse directions.

2.Connected in parallel with the devices.

DIAGRAM 1: Current-voltage characteristics

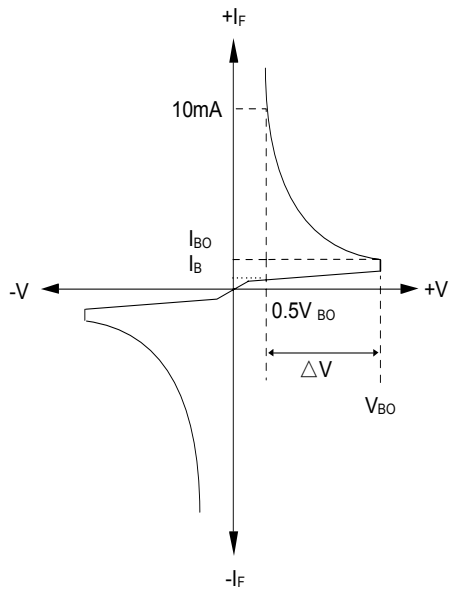


FIG.1-Power dissipation versus ambient temperature (maximum values)

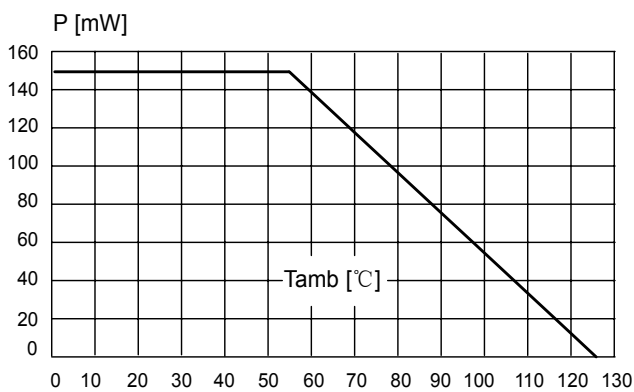


FIG.3-Peck pulse current versus pluse duration (maximum values)

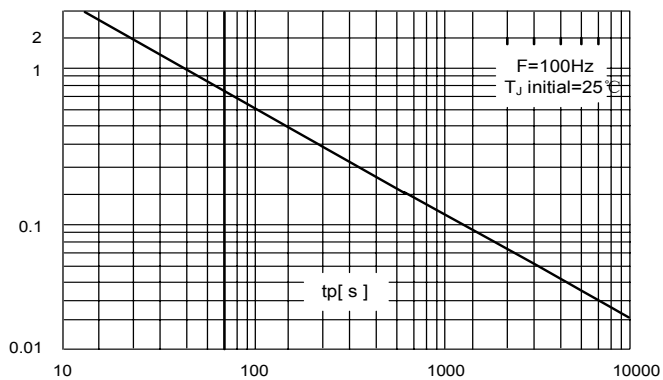


DIAGRAM 2: Test circuit for output voltage

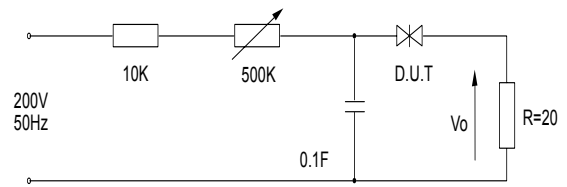


DIAGRAM 3: Test circuit see diagram 2 adjust R for $I_p = 0.5\text{A}$

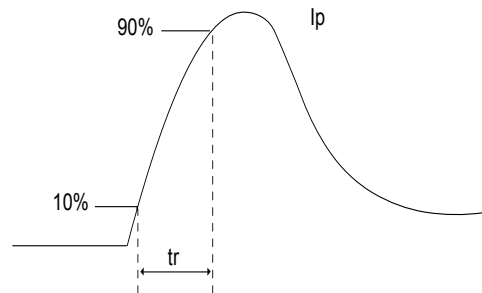


FIG.2-Relative variation of VBO versus junction temperature (typical values)

